



Bipolar NPN Bare Die – BTN6066

Part Description

The BTN6066 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. PNP Complement is BTP6066.

Key Parameters:

- VCBO = 120V
- VCEO = 100V
- VEBO = 6V
- hFE = 140-330 @ VCE = 2V, IC = 0.15A
- VCE(Sat) = 0.5V @ IC = 0.5A, IB = 50mA
- fT = 100 MHz @ VCE = 5V, IE = 0A
- COBO = 10pF @ VCB = 10V

Features

Low VCE(sat)

Die Size (Unawn)

660µm X 660µm, 26 Mils X 26 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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